TOSHIBA Field Effect Transistor Silicon N Channel MOS Type  $(\pi$ -MOSII $^5)$ 

# 2SK1489

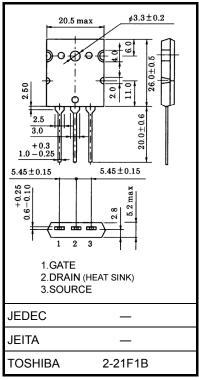
### **Chopper Regulator Applications**

Unit: mm

• Low drain-source ON resistance : RDS (ON) =  $0.8 \Omega$  (typ.) • High forward transfer admittance :  $|Y_{fs}| = 6.0 S$  (typ.) • Low leakage current : IDSS =  $300 \mu A$  (max) (VDS = 800 V) • Enhancement mode :  $V_{th} = 1.5 \sim 3.5 V$  (VDS = 10 V, ID = 1 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteris	tics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	1000	V	
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)		$V_{DGR}$	1000	V	
Gate-source voltage	_	$V_{GSS}$	±30	V	
Drain current	DC (Note 1)	ΙD	12	Α	
	Pulse (Note 1)	$I_{DP}$	36	A	
Drain power dissipation (Tc = 25°C)		$P_{D}$	200	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 9.75 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	0.625	°C / W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	35.7	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device.

Please handle with caution.

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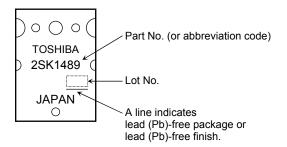
## **Electrical Characteristics (Ta = 25°C)**

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±100	nA
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V	_	_	300	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	1000	_	_	V
Gate threshold v	/oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A	_	0.8	1.0	Ω
Forward transfer	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 6 A	4.0	6.0	_	S
Input capacitano	ce	C <sub>iss</sub>		_	2000	_	
Reverse transfe	r capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	220	_	pF
Output capacita	nce	Coss		_	360	_	
Turn-on Switching time Fall time	Rise time	t <sub>r</sub>	$V_{GS} = \begin{cases} 10V & I_{D} = 6A \\ 0V & R_{L} = 66\Omega \end{cases}$	_	100	_	
	Turn-on time	t <sub>on</sub>		_	140	_	
	Fall time	t <sub>f</sub>	V <sub>DD</sub> ≒400V	_	150	_	ns
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , $t_{\mathbf{W}} = 10 \mu \text{s}$	_	500	_	
Total gate charge (Gate–source plus gate–drain)			_	110	_		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$		50	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>			60	_	

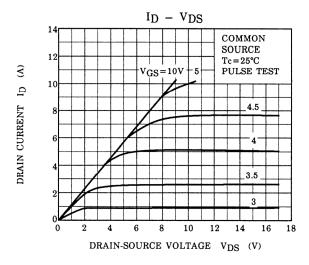
# Source-Drain Ratings and Characteristics (Ta = 25°C)

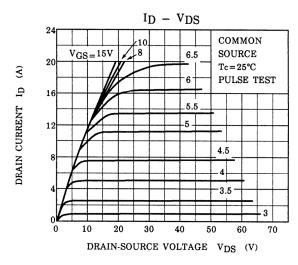
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	-	-	_	12	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	1	ı	ı	36	Α
Forward voltage (diode)	$V_{DSF}$	$I_{DR}$ = 12 A, $V_{GS}$ = 0 V			-1.6	V

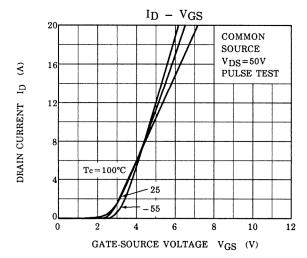
## Marking

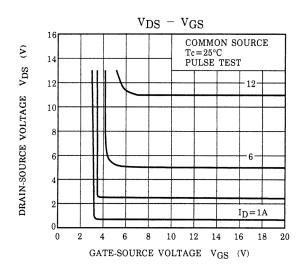


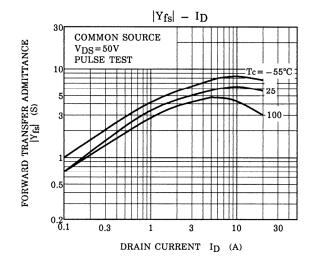
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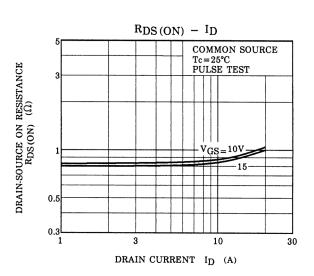


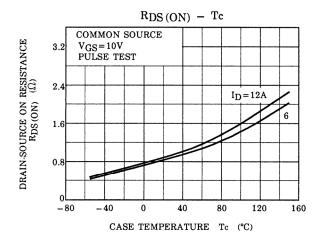


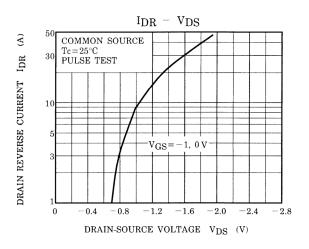


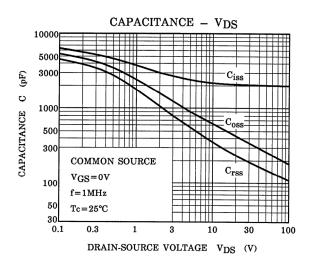


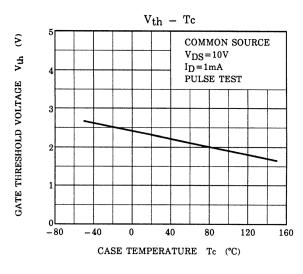


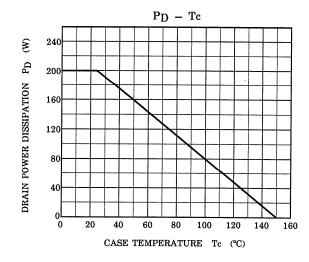


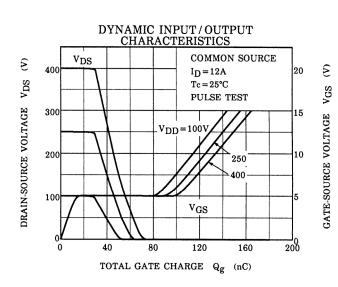


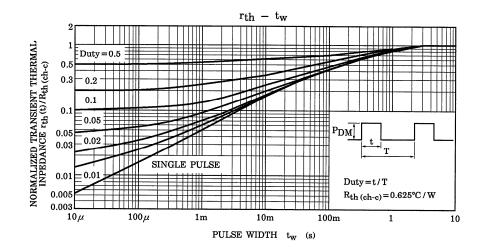


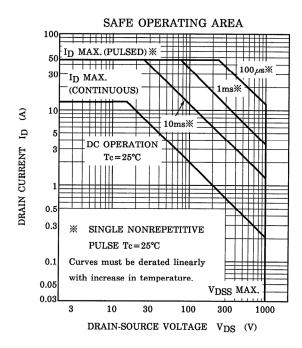












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